

Product Overview

NIS5112: 12 V Electronic Fuse, eFuse

For complete documentation, see the data sheet.



The NIS5112 is an integrated switch utilizing a high side N-channel FET driven by an internal charge pump. This switch features a MOSFET which allows for current sensing using inexpensive chip resistors instead of expensive, low impedance current shunts. It is designed to operate in 12 V systems and includes a robust thermal protection circuit.

Features

- Integrated Power Device
- Power Device Thermally Protected
- No External Current Shunt Required
- Enable/Timer Pin
- Adjustable Slew Rate for Output Voltage
- 9 V to 18 V Input Range
- 30 mΩ Typical
- Internal Charge Pump

Applications

- Hard Drives

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Type	V _I Max (V)	r _{DS(on)} Max (mΩ)	T _{SD} Typ (°C)	T _{hyst} Typ (°C)	Package Type
NIS5112D1R2G	1.32	Pb-free Halide free non AEC-Q and PPAP	Active	Latch Off	18	35	135	40	SOIC-8
NIS5112D2R2G	1.32	Pb-free Halide free non AEC-Q and PPAP	Active	Auto-Retry	18	35	135	40	SOIC-8

For more information please contact your local sales support at www.onsemi.com.

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